

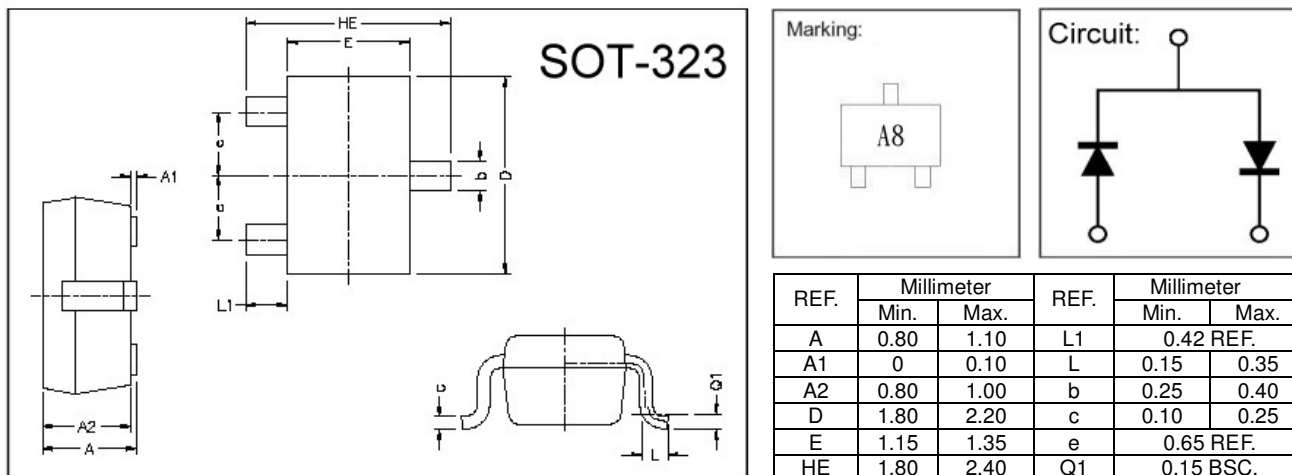
## GS228U

SURFACE MOUNT, SWITCHING DIODE  
 VOLTAGE 80V, CURRENT 0.1A

### Description

The GS228U is designed for bias circuit and protection circuit.

### Package Dimensions



### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T <sub>J</sub>	+150	°C
Storage Temperature	T <sub>stg</sub>	-55 ~ +150	°C
Maximum Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	80	V
Maximum RMS Voltage	V <sub>RMS</sub>	56	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	80	V
Peak Forward Surge Current at 1uSec	I <sub>FSM</sub>	0.3	A
Typical Junction Capacitance between Terminal (Note 1)	C <sub>J</sub>	2.0	pF
Maximum Average Forward Rectified Current	I <sub>o</sub>	0.1	A
Total Power Dissipation	PD	225	mW

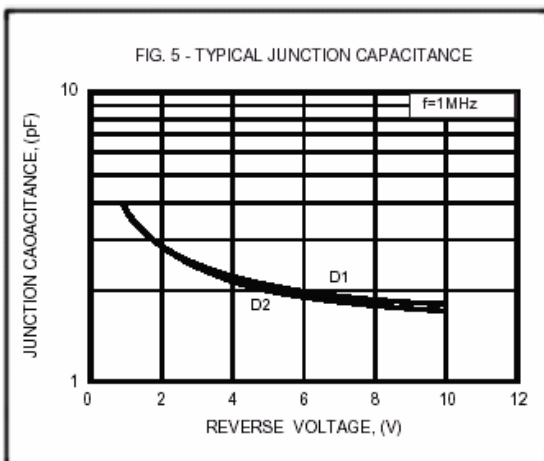
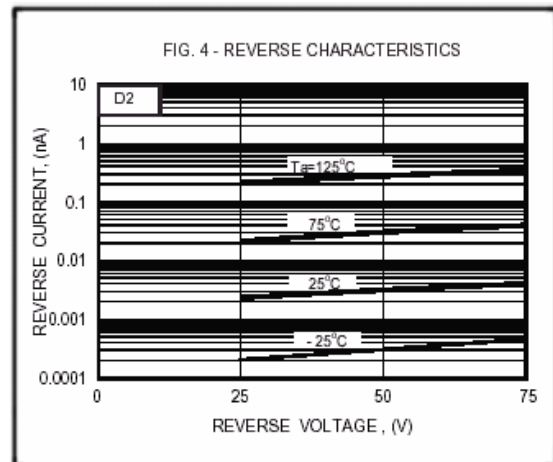
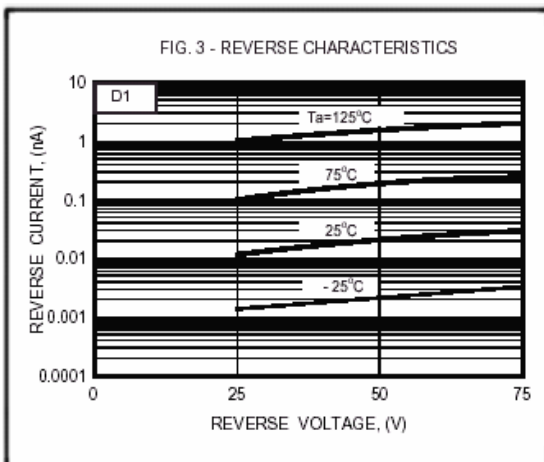
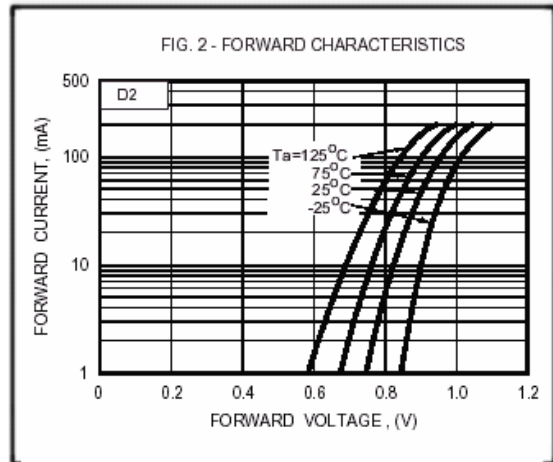
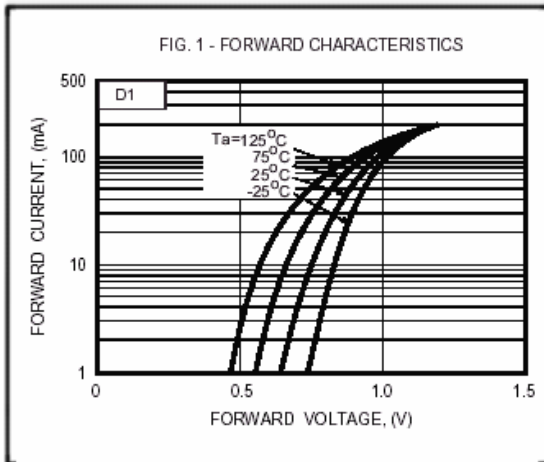
### Characteristics at Ta = 25°C

Characteristics	Symbol	Typ.	Unit	Test Condition
Maximum Instantaneous Forward Voltage	V <sub>F</sub>	1.20	V	I <sub>F</sub> = 100mA
Maximum Average Reverse Current	I <sub>R</sub>	0.1	uA	V <sub>R</sub> = 80V

Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 6.0 volt.

2. ESD sensitive product handling required.

## Characteristics Curve



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